

ABSTRACT**Lithography Method and Apparatus**

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A lithography method and apparatus is disclosed herein. In a described embodiment, the method comprises (i) providing a first mask 316 having an exposure pattern 332,334 for forming a three dimensional structure; (ii) exposing the first mask 316 to radiation to form the exposure pattern 332,334 on a radiation-sensitive resist 314; the exposure pattern 332,334 defined by irradiated areas 336 and non-irradiated areas 337 of the resist 314; (ii) providing a second mask 328; and (iii) during exposure, changing relative positions (arrows B and C) between the first mask 316 and the second mask 328 to shield selected portions of the irradiated areas 336 from radiation to enable varying depth profiles to be created in the three dimensional structure.

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15**Figure 4**